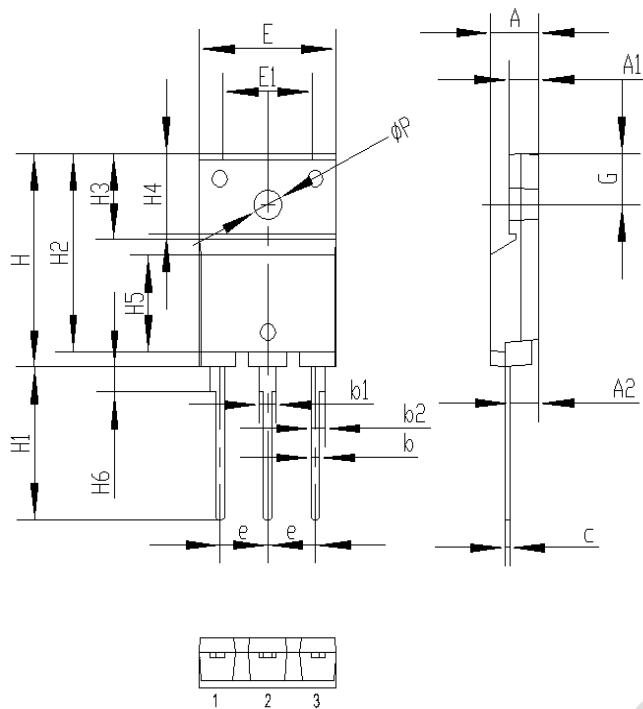
**Typical Applications**

- High power industrial and power transmitter
- DC and AC motor control
- AC controllers

Features

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(RMS)}	RMS on-state current	180° half sine wave 50Hz	125			80	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} , tp=10ms	125			1600	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			10	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			500	A
I ² t	I ² t for fusing coordination					1250	A ² s
V _{TM}	Peak on-state voltage	I _{TM} =160A, tp=380μs	25			2.10	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			1000	V/μs
di/dt	Critical rate of rise of on-state current		125			150	A/μs
I _L	Latching current	I _G =1.2 I _{GT}	25			250	mA
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	20		70	mA
V _{GT}	Gate trigger voltage					1.5	V
I _H	Holding current					200	mA
V _{GD}	Non-trigger gate voltage	V _D =12V	125	0.25			V
R _{th(j-c)}	Thermal resistance Junction to case					0.25	°C /W
T _j	Junction temperature			-40		125	°C
T _{stg}	Stored temperature			-40		150	°C
Outline	TO-3PF						

Outline:

Symbol	Dimensions(millimeters)	
	Min.	Max.
A	5.30	5.70
A1	3.25	3.65
A2	3.15	3.55
b	0.80	1.20
b1	1.85	2.15
b2	1.45	1.75
c	0.40	0.80
e	5.25	5.65
E	15.4	15.8
E1	10.0	10.4
H	22.5	23.2
H1	16.0	17.0
H2	21.2	21.6
H3	9.10	9.50
H4	8.55	8.95
H5	10.20	10.60
H6	2.55	2.85
G	5.30	5.70
ΦP	3.00	3.40